

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

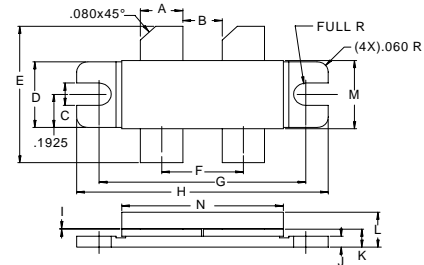
The **ASI BLV859** is Designed for Television Band IV & V Applications up to 860 MHz.

FEATURES:

- Common Emitter
- $P_G = 10$ dB at 150 W/860 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	15 A
V_{CEO}	28 V
V_{CBO}	60 V
V_{EBO}	2.5 V
P_{DISS}	145 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.20 °C/W

PACKAGE STYLE .400 BAL FLG(C)


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.210 / 5.33	
C	.120 / 3.05	.130 / 3.30
D	.380 / 9.65	.390 / 9.91
E	.780 / 19.81	.820 / 20.83
F	.435 / 11.05	
G	1.090 / 27.69	
H	1.335 / 33.91	1.345 / 34.16
I	.003 / 0.08	.007 / 0.18
J	.060 / 1.52	.070 / 1.78
K	.082 / 2.08	.100 / 2.54
L		.205 / 5.21
M	.395 / 10.03	.407 / 10.34
N	.850 / 21.59	.870 / 22.10

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 30$ mA	60			V
BV_{CEO}	$I_C = 60$ mA	28			V
BV_{EBO}	$I_E = 1.2$ mA	2.5			V
I_{CBO}	$V_{CB} = 27$ V			3.0	mA
I_{CEO}	$V_{CE} = 20$ V			6.0	mA
h_{FE}	$V_{CE} = 25$ V $I_C = 2.25$ A	30		140	---
C_{OB}	$V_{CB} = 26$ V $f = 1.0$ MHz		75		pF
P_G IMD_1	$V_{CC} = 25$ V $I_{CQ} = 2 \times 2.25$ A $f = 860$ MHz $P_{OUT} = 20$ W	10		-54	dB dBc
$VSRW$	$V_{CC} = 25$ V $I_{CQ} = 2 \times 2.25$ A $P_{OUT} = 20$ W PEP $VSWR = 50:1$ @ all phase angles	No Degradation in Output Power			